

/ Descriptions

WR0<5 M M E QSQ æ M ı s ll 1 Silicon NPN transistor in a TO-92 Plastic Package.

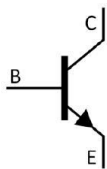
/ Features

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High transition frequency, low output capacitance.

/ Applications

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RF amplifier applications.

/ Equivalent Circuit



/ Pinning



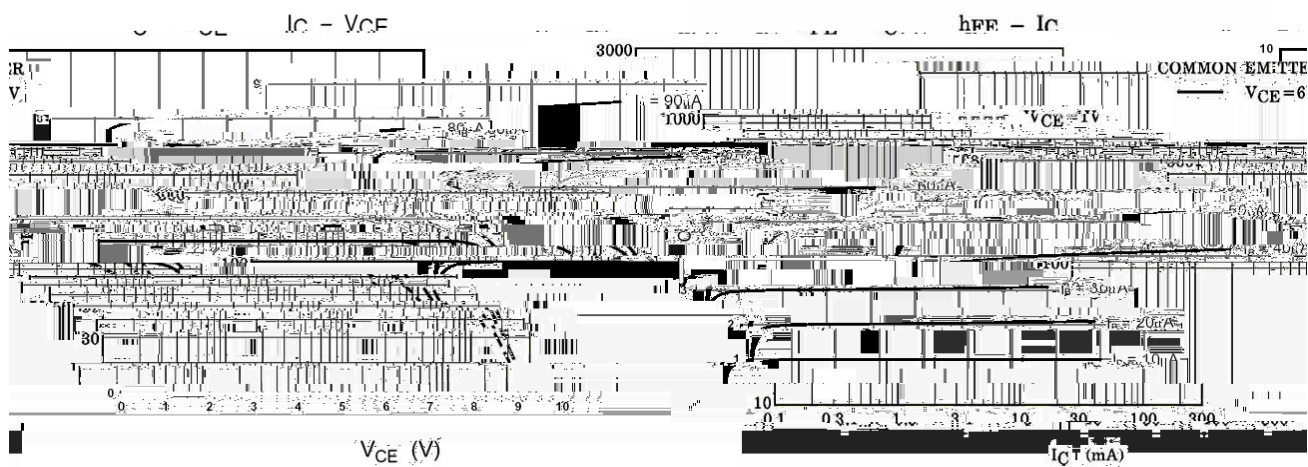
PIN1 χ Base PIN 2 χ Collector PIN 3 χ Emitter

/ hFE Classifications & Marking

h _{FE} Classifications Symbol	R	O	Y
h _{FE} Range	40~80	70~140	120~240

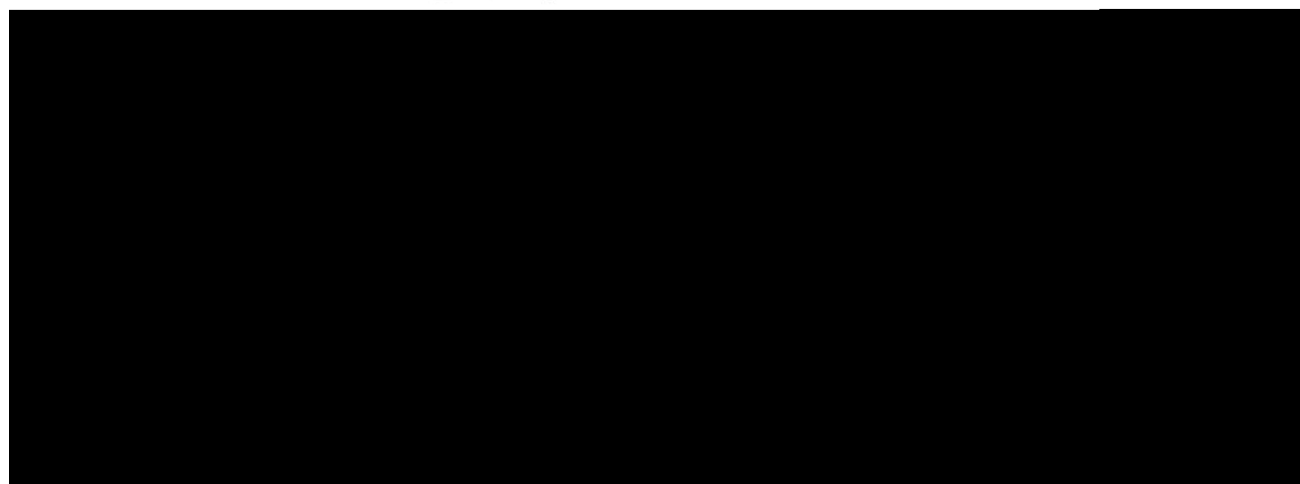
Parameter	Symbol	Rating	Unit
Collector to Base Voltage	V_{CBO}	30	V
Collector to Emitter Voltage	V_{CEO}	20	V
Emitter to Base Voltage	V_{EBO}	4.0	V
Collector Current - Continuous	I_C		

Electrical Characteristic Curve

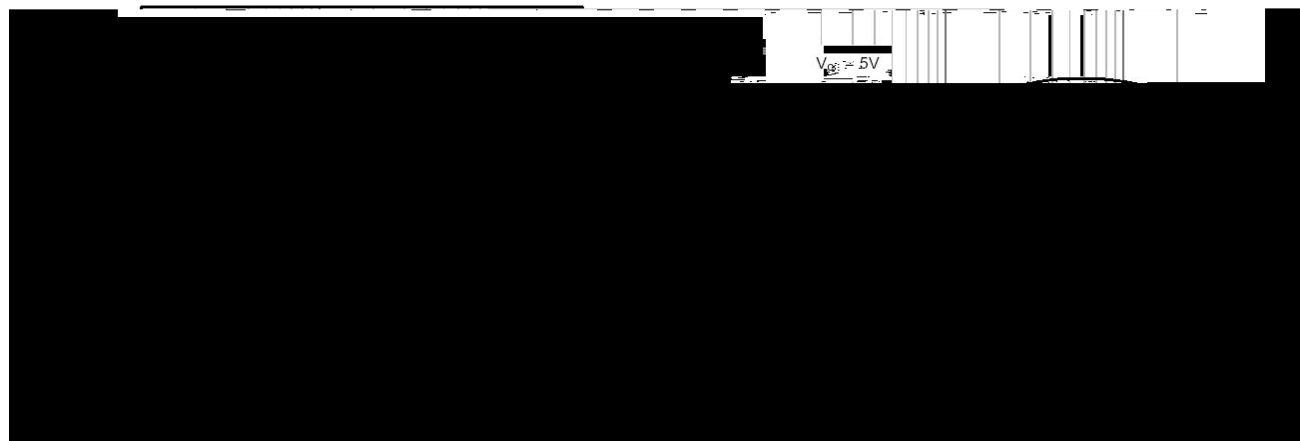


$V_{CE(sat)} - I_{C(sat)} = 10$

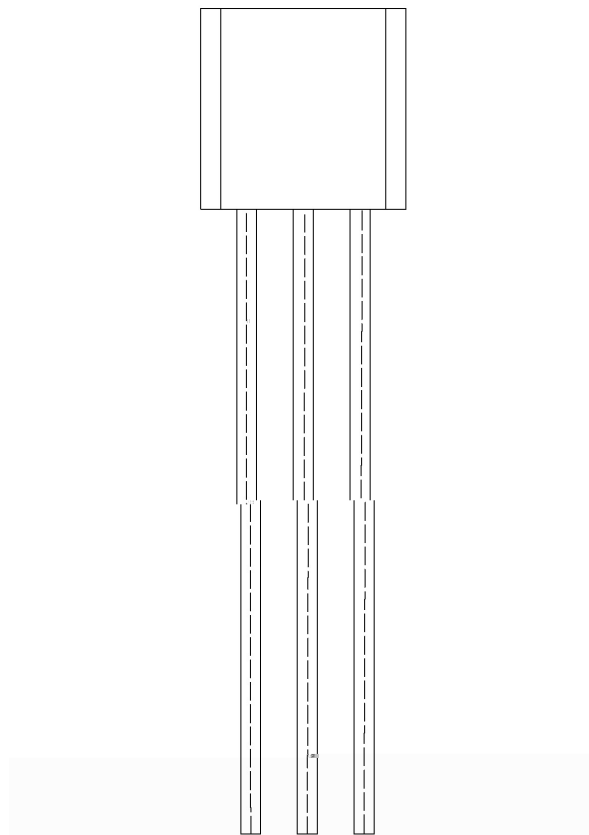
$C_{ob} - V_{CE} = 10$



$f_T - I_C$

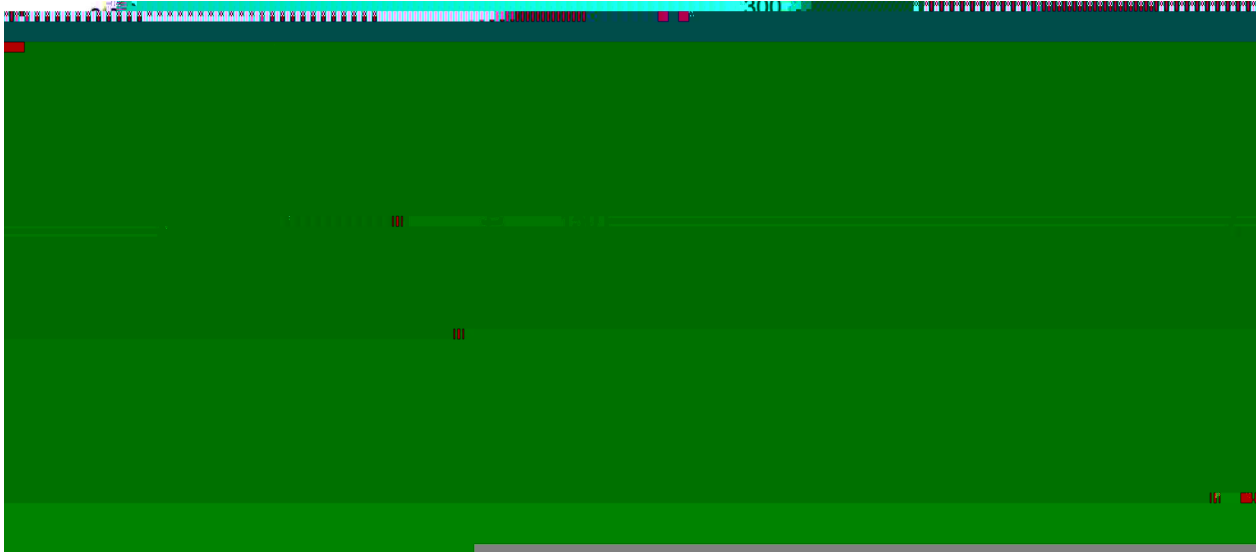


/ Marking Instructions


$$U =$$

h_{FE} Classifications Symbol.

() / Temperature Profile for Dip Soldering(Pb-Free)



说明

1. 预加热: 25~150 °C, 时间: 60~90sec;
2. 峰值温度: 255 °C, 持续时间: 5~0.5sec;
3. 冷却速度: 2~10 °C/sec.

Note:

- 1.Preheating:25~150 °C , Time:60~90sec.
- 2.Peak Temp.:255 °C , Duration:5 °C 0.5sec.
3. Cooling Speed: 2~10 °C/sec.

/ Resistance to Soldering Heat Test Conditions

说明: 270 °C ± 5 °C, 时间: 10 ± 1 sec. Temp:270±5 Time:10±1 sec

/ Packaging SPEC.

说明: / BULK

Package Type	Units					Dimension (unit mm3)		
	Units/Bag	Bags/Inner Box	Units/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Bag	Inner Box	Outer Box
TO-92	1,000	10	10,000	5	50,000	135×190	237×172×102	560×245×195
	1,000	10	10,000	10	100,000	135×190	237×172×102	560×245×375

说明: / AMMO

Package Type	Units					Dimension (unit mm3)	
	Units/tape	Tape/Inner Box	Rows/Inner Box	Inner Boxes/Outer Box	Units/Outer Box	Inner Box	Outer Box
TO-92	3,000	1	120	10	30,000	328×230×42	480×346×235
							547×407×268

/ Notices